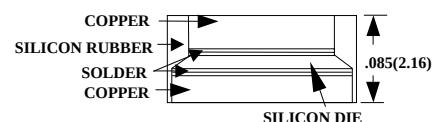
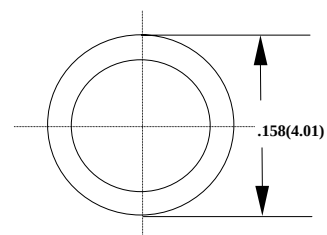


3A SILICON RECTIFIER CELL

FEATURES

- IDEAL FOR HYBRID CIRCUITS
- SOLDER MOUNTING SURFACES
- TYPICAL I_R LESS THAN $1\mu A$
- DIFFUSED JUNCTION
- HIGH SURGE CAPABILITY
- MOUNTING POSITION : ANY

CELL DESIGNATION : A SUFFIX LETTER IS ADDED TO THE PRIMARY CELL DESIGNATION TO INDICATES THE CELL VOLTAGE



PR4 PACKAGE

DIMENSIONS IN INCHES AND (MILLIMETERS)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
RATINGS AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE SPECIFIED
SINGLE PHASE, HALF WAVE, 60 HZ, RESISTIVE OR INDUCTIVE LOAD.
FOR CAPACITIVE LOAD, DERATE CURRENT BY 20%

RATINGS	SYMBOL	005	01	02	04	06	08	10	UNITS
MAXIMUM RECURRENT PEAK REVERSE VOLTAGE	V_{RRM}	50	100	200	400	600	800	1000	V
MAXIMUM RMS VOLTAGE	V_{RMS}	35	70	140	280	420	560	700	V
MAXIMUM DC BLOCKING VOLTAGE	V_{DC}	50	100	200	400	600	800	1000	V
MAXIMUM AVERAGE FORWARD RECTIFIER CURRENT @ TC 100°C	I_O	3.0							A
PEAK FORWARD SURGE CURRENT 8.3m SINGLE HALF SINE-WAVE SUPERIMPOSED ON RATED LOAD JEDEC METHOD	I_{FSM}	150							A
STORAGE TEMPERATURE RANGE	T_{STG}	- 55 TO + 150							°C
OPERATING TEMPERATURE RANGE	T_{OP}	- 55 TO + 150							°C

ELECTRICAL CHARACTERISTICS (@ $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

CHARACTERISTICS	SYMBOL	005	01	02	04	06	08	10	UNITS
MAXIMUM FORWARD VOLTAGE AT SPECIFIED CURRENT SC30 @ IF 3.0A	V_F	1.2							V
MAXIMUM REVERSE LEAKAGE CURRENT AT RATED DC BLOCKING VOLTAGE	I_R	10							μA